

CMP4N150B/CMF4N150B

1500V, 5.9Ω typ., 4A N-Channel MOSFET

General Description

The 4N150B uses advanced planar stripe DMOS technology and design to provide excellent RDS(ON).

These devices are well suited for high efficiency switch mode power supply.

Features

- 100% avalanche tested
- Improved dv/dt capability
- RoHS Compliant

Product Summary

BVDSS	R _{DS(on)} max.	ID
1500V	7Ω	4A

Applications

- Switching applications

TO-220/220F Pin Configuration



Absolute Maximum Ratings

Symbol	Parameter	220	220F	Units
V _{DS}	Drain-Source Voltage	1500		V
V _{GS}	Gate-Source Voltage	±30		V
I _D @T _C =25°C	Continuous Drain Current	4	4*	A
I _D @T _C =100°C	Continuous Drain Current	2.8	2.8*	A
I _{DM}	Pulsed Drain Current	16	16*	A
EAS	Single Pulse Avalanche Energy (Note 1)	473		mJ
P _D @T _C =25°C	Total Power Dissipation	150	40	W
T _{STG}	Storage Temperature Range	-55 to 150		°C
T _J	Operating Junction Temperature Range	-55 to 150		°C

* Drain current limited by maximum junction temperature.

Thermal Data

Symbol	Parameter	220	220F	Unit
R _{θJA}	Thermal Resistance Junction-ambient Max.	62.5	62.5	°C/W
R _{θJC}	Thermal Resistance Junction-case Max.	0.83	3.13	°C/W

Electrical Characteristics ($T_J=25^{\circ}\text{C}$, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=250\mu A$	1500	---	---	V
$R_{DS(ON)}$	Static Drain-Source On-Resistance	$V_{GS}=10V, I_D=2A$	---	5.9	7	Ω
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS}=V_{DS}, I_D=250\mu A$	3	---	5	V
I_{DSS}	Drain-Source Leakage Current	$V_{DS}=1500V, V_{GS}=0V$	---	---	10	μA
I_{GSS}	Gate-Source Leakage Current	$V_{GS}=\pm 30V, V_{DS}=0V$	---	---	± 100	nA
g_{fs}	Forward Transconductance	$V_{DS}=30V, I_D=2A$	---	4	---	S
R_g	Gate Resistance	$V_{DS}=0V, V_{GS}=0V, f=1\text{MHz}$	---	2.2	---	Ω
Q_g	Total Gate Charge	$V_{DS}=600V, I_D=4A$ $V_{GS}=0$ to 10V	---	30	---	nC
Q_{gs}	Gate-Source Charge		---	8	---	
Q_{gd}	Gate-Drain Charge		---	12	---	
$T_{d(on)}$	Turn-On Delay Time	$V_{DD}=750V, I_D=2A$ $R_{GS}=4.7\Omega, V_{GS}=10V$	---	34	---	ns
T_r	Rise Time		---	31	---	
$T_{d(off)}$	Turn-Off Delay Time		---	47	---	
T_f	Fall Time		---	45	---	
C_{iss}	Input Capacitance	$V_{DS}=25V, V_{GS}=0V, f=1\text{MHz}$	---	1200	---	pF
C_{oss}	Output Capacitance		---	100	---	
C_{riss}	Reverse Transfer Capacitance		---	10	---	

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I_S	Continuous Source Current	$V_G=V_D=0V$, Force Current	---	---	4	A
I_{SM}	Pulsed Source Current		---	---	16	A
V_{SD}	Diode Forward Voltage	$V_{GS}=0V, I_S=4A$	---	0.82	1.5	V

Note :

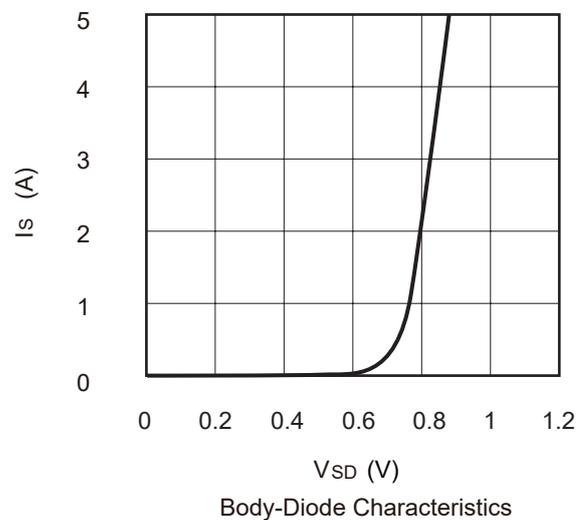
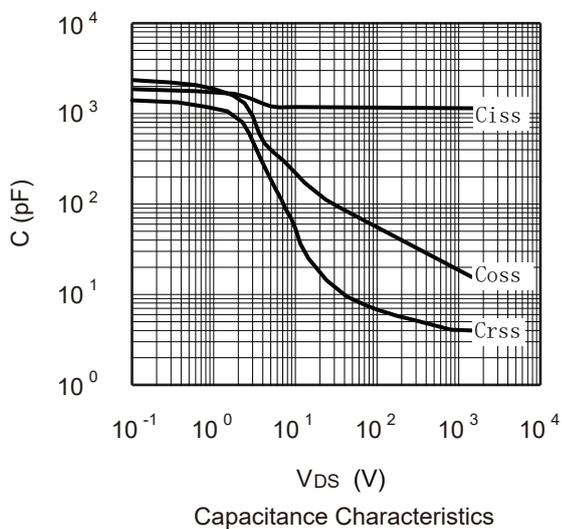
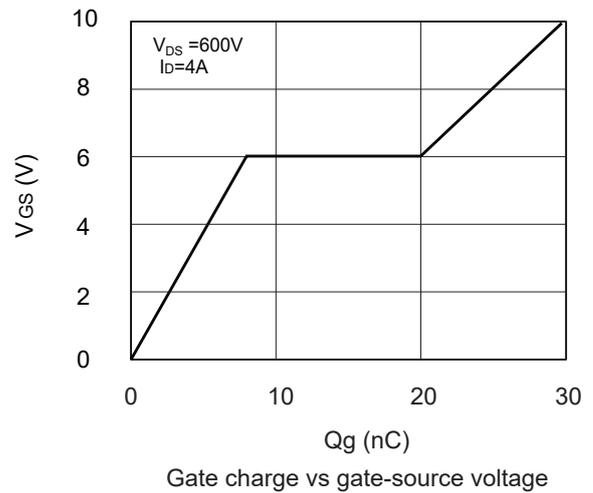
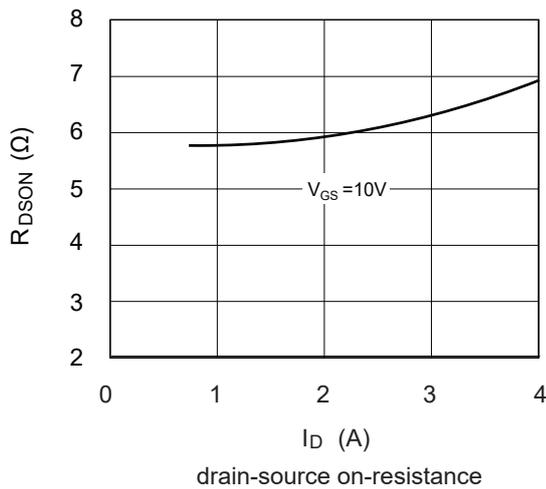
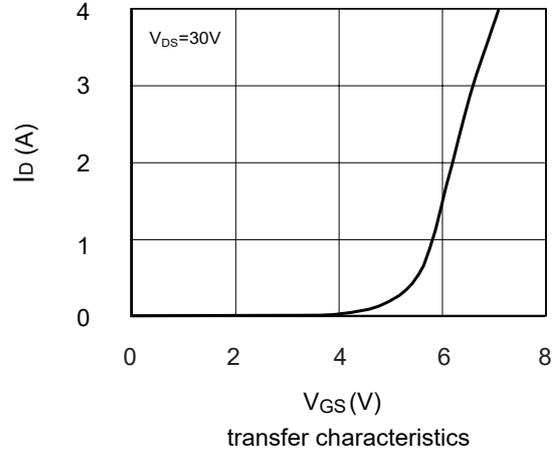
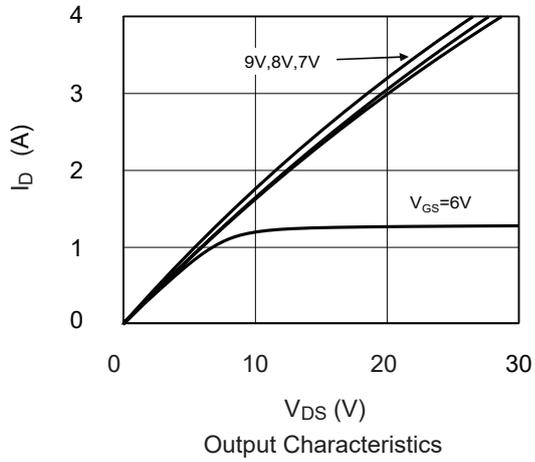
1.The EAS data shows Max. rating .The test condition is $V_{DS}=100V, V_{GS}=10V, L=35\text{mH}, I_{AS}=5.2A$.

This product has been designed and qualified for the consumer market.

Cmos assumes no liability for customers' product design or applications.

Cmos reserves the right to improve product design ,functions and reliability without notice.Please refer to the latest version of specification.

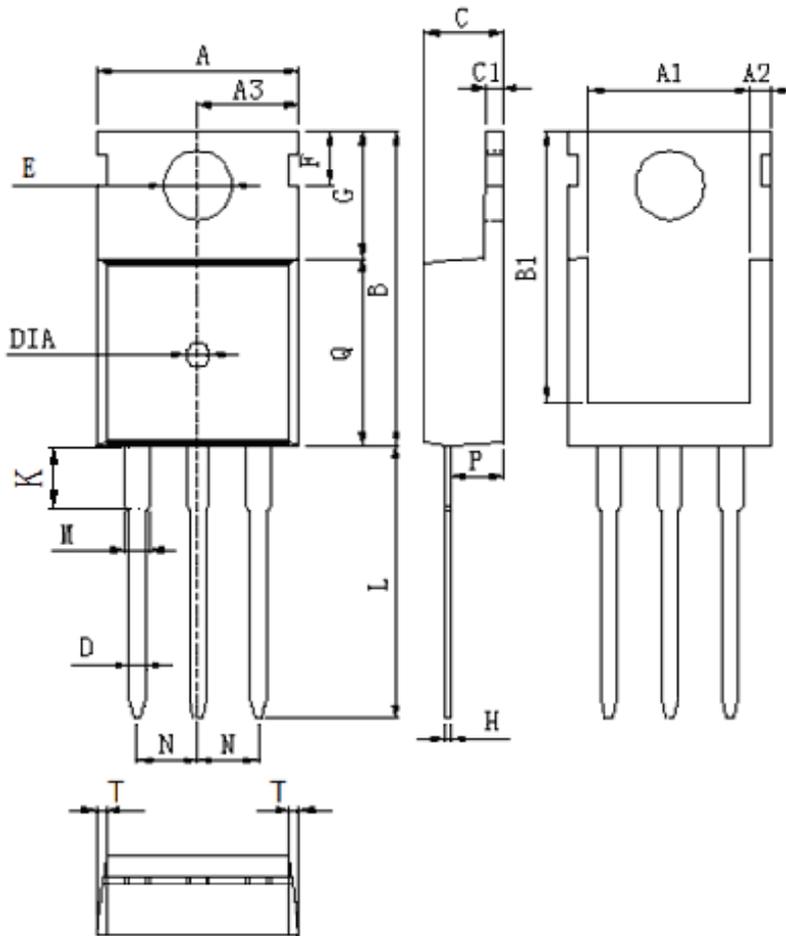
Typical Characteristics



Package Dimension

TO-220

Unit :mm

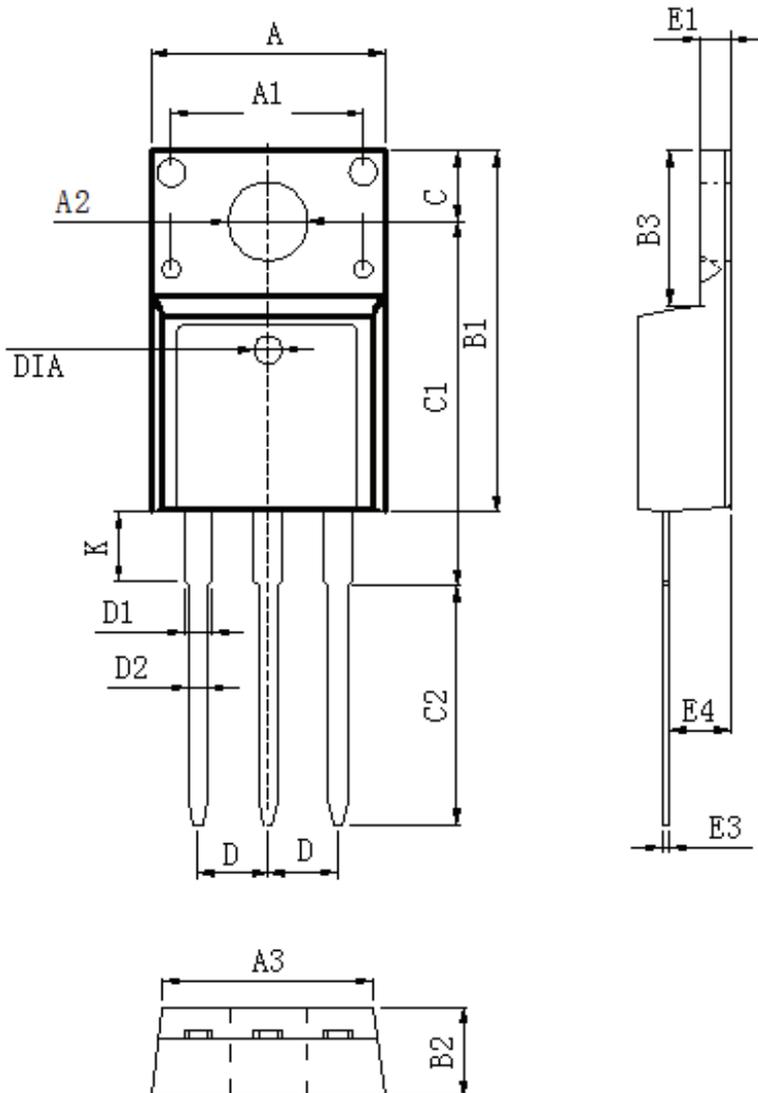


DIM	MILLIMETERS
A	10.0±0.3
A1	8.64±0.2
A2	1.15±0.1
A3	5.0±0.2
B	15.8±0.4
B1	13.2±0.3
C	4.56±0.1
C1	1.3±0.2
D	0.8±0.2
E	3.6±0.2
F	2.95±0.3
G	6.5±0.3
H	0.5±0.1
K	3.1±0.2
L	13.2±0.4
M	1.25±0.1
N	2.54±0.1
P	2.4±0.3
Q	9.0±0.3
T	W:0.35
DIA	⊙1.5(deep 0.2)

Package Dimension

TO-220F

Unit :mm



DIM	MILLIMETERS
A	10.16±0.3
A1	7.00±0.1
A2	3.3±0.2
A3	9.5±0.2
B1	15.87±0.3
B2	4.7±0.2
B3	6.68±0.4
C	3.3±0.2
C1	12.57±0.3
C2	10.02±0.5
D	2.54±0.05
D1	1.28±0.2
D2	0.8±0.1
K	3.1±0.3
E1	2.54±0.1
E3	0.5±0.1
E4	2.76±0.2
DIA	⊙1.5 (deep 0.2)